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a first conductive layer formed on said first insulating film;  
a second conductive layer formed on said first conductive layer;  
a second insulating film formed on said second conductive layer; and  
a pixel electrode formed on said second insulating film, said pixel electrode being connected  
to said second conductive layer through a contact hole provided in said second insulating film,  
wherein said second conductive layer is directly connected to said semiconductor layer  
through a contact hole provided in said first insulating film.

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Sub  
F5

34. (Third Amendment) A semiconductor device comprising:  
a thin film transistor formed over a substrate, said thin film transistor having a semiconductor  
layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed  
therebetween;  
a first insulating film comprising an organic material formed over said thin film transistor;  
a first conductive layer formed on said first insulating film;  
a second conductive layer formed on said first conductive layer;  
a second insulating film formed on said second conductive layer; and  
a pixel electrode formed on said second insulating film, said pixel electrode being connected  
to said second conductive layer through a contact hole provided in said second insulating film,  
wherein said second conductive layer is directly connected to said semiconductor layer  
through a contact hole provided in said first conductive layer and said first insulating film.

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